Infineon Technologies - XMC1100T016F0008ABXUMA1 Datasheet

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, I²S, POR, PWM, WDT
Number of I/O	11
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 6x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	16-TSSOP (0.173", 4.40mm Width)
Supplier Device Package	PG-TSSOP-16-8
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xmc1100t016f0008abxuma1

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About this Document

This Data Sheet is addressed to embedded hardware and software developers. It provides the reader with detailed descriptions about the ordering designations, available features, electrical and physical characteristics of the XMC1100 series devices.

The document describes the characteristics of a superset of the XMC1100 series devices. For simplicity, the various device types are referred to by the collective term XMC1100 throughout this document.

XMC™1000 Family User Documentation

The set of user documentation includes:

- **Reference Manual**
  – decribes the functionality of the superset of devices.
- **Data Sheets**
  – list the complete ordering designations, available features and electrical characteristics of derivative devices.
- **Errata Sheets**
  – list deviations from the specifications given in the related Reference Manual or Data Sheets. Errata Sheets are provided for the superset of devices.

Attention: Please consult all parts of the documentation set to attain consolidated knowledge about your device.

Application related guidance is provided by **Users Guides** and **Application Notes**.

Please refer to **http://www.infineon.com/xmc1000** to get access to the latest versions of those documents.

1 Summary of Features

The XMC1100 devices are members of the XMC™1000 Family of microcontrollers based on the ARM Cortex-M0 processor core. The XMC1100 series devices are designed for general purpose applications.

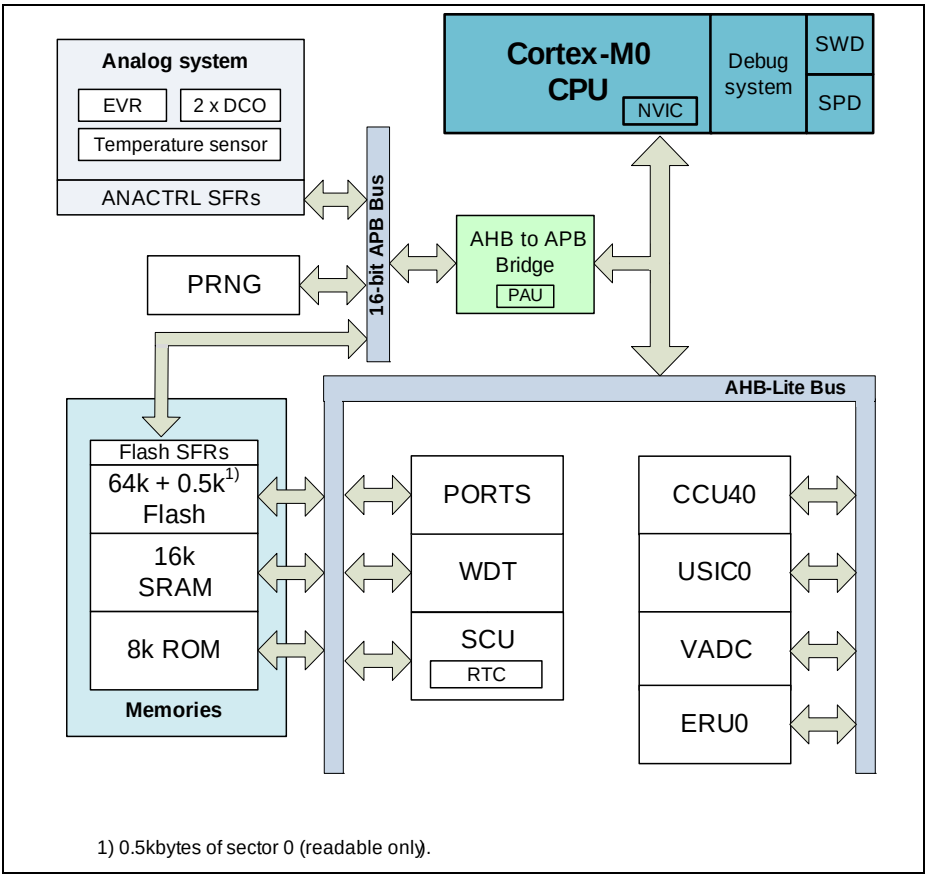

Figure 1 System Block Diagram

CPU Subsystem

- CPU Core
  - High-performance 32-bit ARM Cortex-M0 CPU
  - Most 16-bit Thumb and subset of 32-bit Thumb2 instruction set
  - Single cycle 32-bit hardware multiplier

  - Q: VQFN
- <PPP> package pin count
- <T> the temperature range:
  - F: -40°C to 85°C
  - X: -40°C to 105°C
- <FFFF> the Flash memory size.

For ordering codes for the XMC1100 please contact your sales representative or local distributor.

This document describes several derivatives of the XMC1100 series, some descriptions may not apply to a specific product. Please see **Table 1**.

For simplicity the term **XMC1100** is used for all derivatives throughout this document.

1.2 Device Types

These device types are available and can be ordered through Infineon's direct and/or distribution channels.

Table 1 Synopsis of XMC1100 Device Types

Derivative	Package	Flash Kbytes	SRAM Kbytes
XMC1100-T016F0008	PG-TSSOP-16-8	8	16
XMC1100-T016F0016	PG-TSSOP-16-8	16	16
XMC1100-T016F0032	PG-TSSOP-16-8	32	16
XMC1100-T016F0064	PG-TSSOP-16-8	64	16
XMC1100-T016X0016	PG-TSSOP-16-8	16	16
XMC1100-T016X0032	PG-TSSOP-16-8	32	16
XMC1100-T016X0064	PG-TSSOP-16-8	64	16
XMC1100-T038F0016	PG-TSSOP-38-9	16	16
XMC1100-T038F0032	PG-TSSOP-38-9	32	16
XMC1100-T038F0064	PG-TSSOP-38-9	64	16
XMC1100-T038X0064	PG-TSSOP-38-9	64	16
XMC1100-Q024F0008	PG-VQFN-24-19	8	16
XMC1100-Q024F0016	PG-VQFN-24-19	16	16
XMC1100-Q024F0032	PG-VQFN-24-19	32	16
XMC1100-Q024F0064	PG-VQFN-24-19	64	16
XMC1100-Q040F0016	PG-VQFN-40-13	16	16

2.2 Pin Configuration and Definition

The following figures summarize all pins, showing their locations on the different packages.

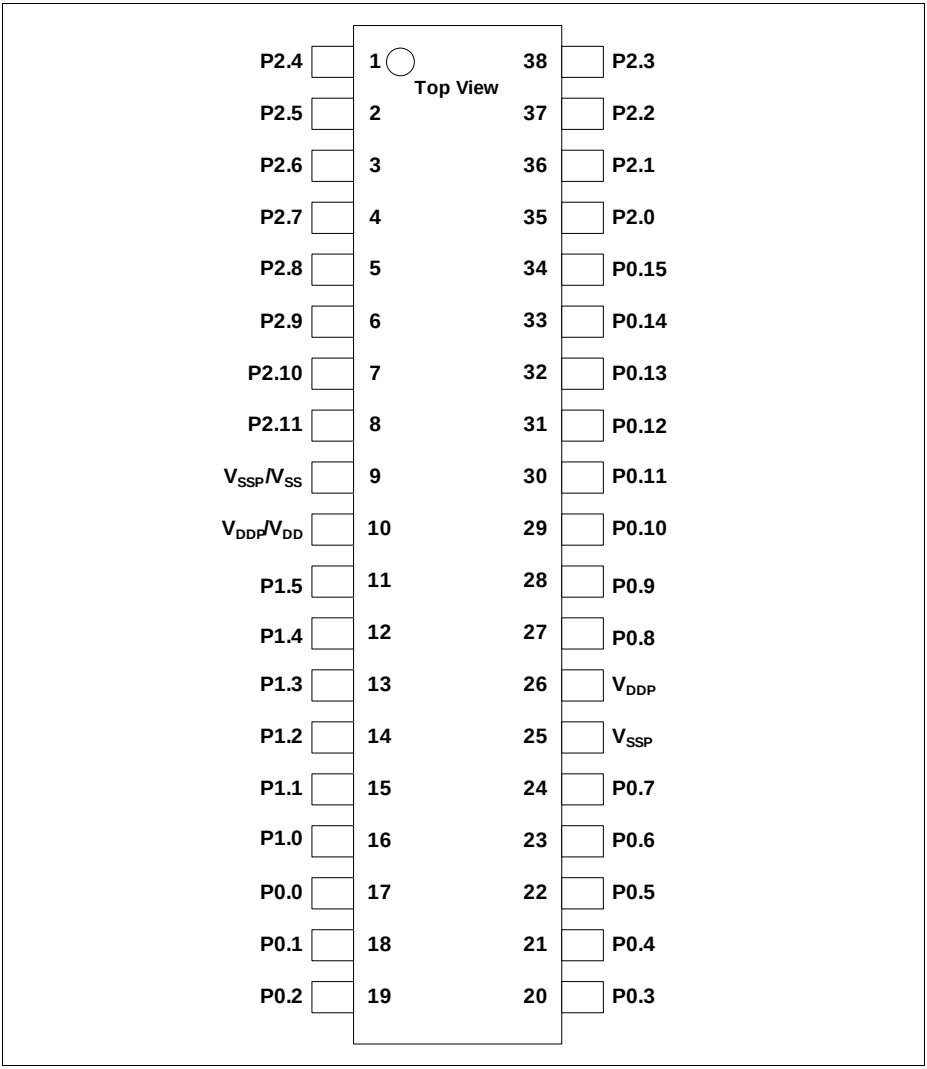

Figure 4 XMC1100 PG-TSSOP-38 Pin Configuration (top view)

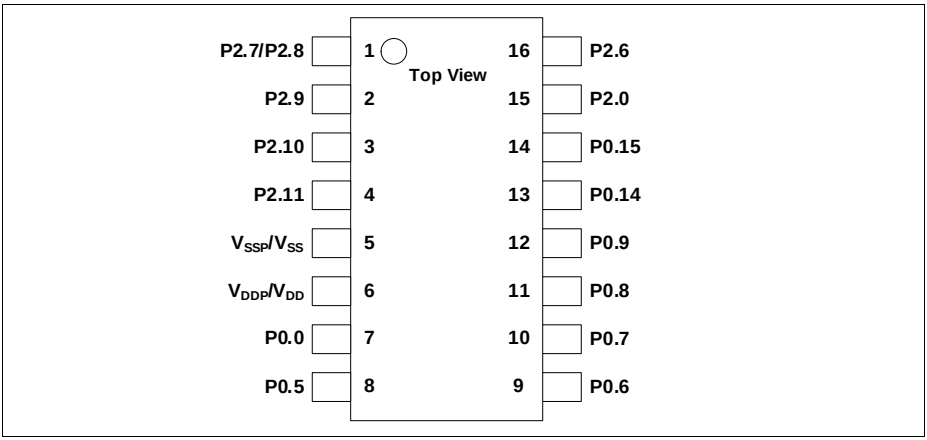

Figure 5 XMC1100 PG-TSSOP-16 Pin Configuration (top view)

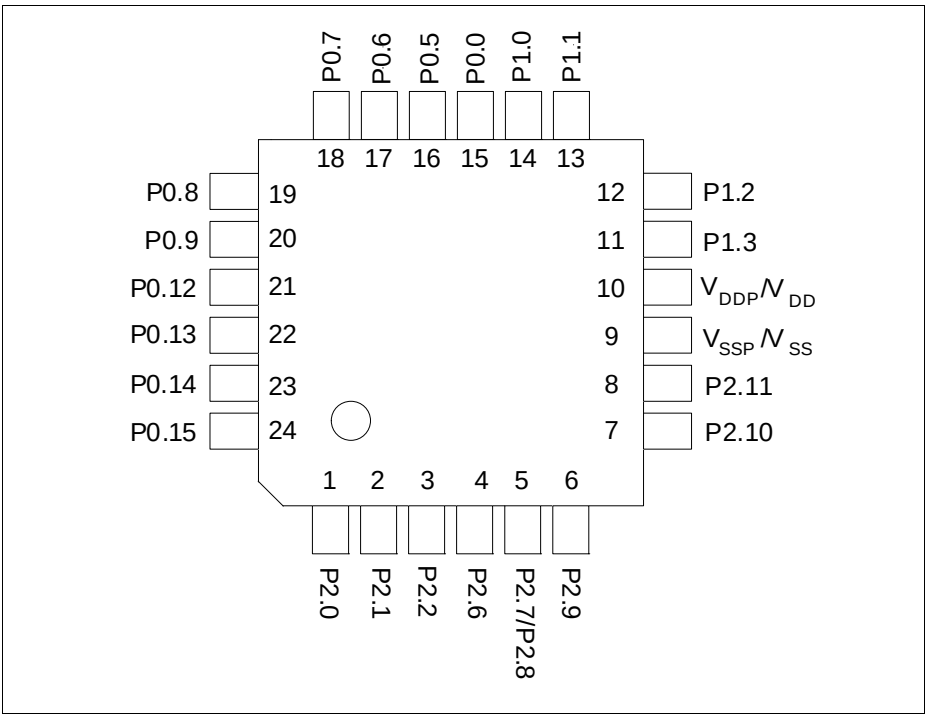

Figure 6 XMC1100 PG-VQFN-24 Pin Configuration (top view)

Table 6 Package Pin Mapping (cont'd)

Function	VQFN 40	TSSOP 38	VQFN 24	TSSOP 16	Pad Type	Notes
VDDP	15	10	10	6	Power	When VDD is supplied, VDDP has to be supplied with the same voltage.
VSSP	31	25	-	-	Power	I/O port ground
VDDP	32	26	-	-	Power	I/O port supply
VSSP	Exp. Pad	-	Exp. Pad	-	Power	**Exposed Die Pad** The exposed die pad is connected internally to VSSP. For proper operation, it is mandatory to connect the exposed pad to the board ground. For thermal aspects, please refer to the Package and Reliability chapter.

2.2.2 Port I/O Function Description

The following general building block is used to describe the I/O functions of each PORT pin:

Table 7 Port I/O Function Description

Function	Outputs		Inputs	
	ALT1	ALTn	Input	Input
P0.0		MODA.OUT	MODC.INA	
Pn.y	MODA.OUT		MODA.INA	MODC.INB

Table 9 Port I/O Functions

Function	Outputs							Inputs						
	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	Input	Input	Input	Input	Input	Input	Input
P0.0	ERU0.PDOUT0		ERU0.GOUT0	CCU40.OUT0		USIC0_CH0.SELO0	USIC0_CH1.SELO0	CCU40.IN0C				USIC0_CH0.DX2A	USIC0_CH1.DX2A	
P0.1	ERU0.PDOUT1		ERU0.GOUT1	CCU40.OUT1			SCU.VDROP	CCU40.IN1C						
P0.2	ERU0.PDOUT2		ERU0.GOUT2	CCU40.OUT2		VADC0.EMUX02		CCU40.IN2C						
P0.3	ERU0.PDOUT3		ERU0.GOUT3	CCU40.OUT3		VADC0.EMUX01		CCU40.IN3C						
P0.4				CCU40.OUT1		VADC0.EMUX00	WWDT.SERVICE_OUT							
P0.5				CCU40.OUT0										
P0.6				CCU40.OUT0		USIC0_CH1.MCLKOUT	USIC0_CH1.DOUT0	CCU40.IN0B				USIC0_CH1.DX0C		
P0.7				CCU40.OUT1		USIC0_CH0.SCLKOUT	USIC0_CH1.DOUT0	CCU40.IN1B				USIC0_CH0.DX1C	USIC0_CH1.DX0D	USIC0_CH1.DX1C
P0.8				CCU40.OUT2		USIC0_CH0.SCLKOUT	USIC0_CH1.SCLKOUT	CCU40.IN2B				USIC0_CH0.DX1B	USIC0_CH1.DX1B	
P0.9				CCU40.OUT3		USIC0_CH0.SELO0	USIC0_CH1.SELO0	CCU40.IN3B				USIC0_CH0.DX2B	USIC0_CH1.DX2B	
P0.10						USIC0_CH0.SELO1	USIC0_CH1.SELO1					USIC0_CH0.DX2C	USIC0_CH1.DX2C	
P0.11				USIC0_CH0.MCLKOUT		USIC0_CH0.SELO2	USIC0_CH1.SELO2					USIC0_CH0.DX2D	USIC0_CH1.DX2D	
P0.12						USIC0_CH0.SELO3		CCU40.IN0A	CCU40.IN1A	CCU40.IN2A	CCU40.IN3A	USIC0_CH0.DX2E		
P0.13	WWDT.SERVICE_OUT					USIC0_CH0.SELO4						USIC0_CH0.DX2F		
P0.14						USIC0_CH0.DOUT0	USIC0_CH0.SCLKOUT					USIC0_CH0.DX0A	USIC0_CH0.DX1A	
P0.15						USIC0_CH0.DOUT0	USIC0_CH1.MCLKOUT					USIC0_CH0.DX0B		
P1.0		CCU40.OUT0					USIC0_CH0.DOUT0					USIC0_CH0.DX0C		

Table 10 Hardware Controlled I/O Functions

Function	Outputs		Inputs		Pull Control			
	HWO0	HWO1	HWI0	HWI1	HW0_PD	HW0_PU	HW1_PD	HW1_PU
P0.0								
P0.1								
P0.2								
P0.3								
P0.4								
P0.5								
P0.6								
P0.7								
P0.8								
P0.9								
P0.10								
P0.11								
P0.12								
P0.13								
P0.14								
P0.15								
P1.0		USIC0_CH0. DOUT0		USIC0_CH0. HWIN0				
P1.1		USIC0_CH0. DOUT1		USIC0_CH0. HWIN1				
P1.2		USIC0_CH0. DOUT2		USIC0_CH0. HWIN2				
P1.3		USIC0_CH0. DOUT3		USIC0_CH0. HWIN3				
P1.4								
P1.5								
P1.6								
P2.0								
P2.1								
P2.2							$\overline{\text{CCU40.OUT3}}$	CCU40.OUT3
P2.3								
P2.4								

Table 13 PN-Junction Characterisitics for positive Overload

Pad Type	I_{OV} = 5 mA, T_J = -40 °C	I_{OV} = 5 mA, T_J = 115 °C
Standard, High-current, AN/DIG_IN	$V_{IN} = V_{DDP}$ + 0.5 V	$V_{IN} = V_{DDP}$ + 0.5 V

Table 14 PN-Junction Characterisitics for negative Overload

Pad Type	I_{OV} = 5 mA, T_J = -40 °C	I_{OV} = 5 mA, T_J = 115 °C
Standard, High-current, AN/DIG_IN	$V_{IN} = V_{SS}$ - 0.5 V	$V_{IN} = V_{SS}$ - 0.5 V

Table 16 Input/Output Characteristics (Operating Conditions apply) (cont'd)

Parameter	Symbol		Limit Values		Unit	Test Conditions
			Min.	Max.		
Pin capacitance (digital inputs/outputs)	C_{IO}	CC	–	10	pF	
Pull-up resistor on port pins	R_{PUP}	CC	20	50	kohm	$V_{IN} = V_{SSP}$
Pull-down resistor on port pins	R_{PDP}	CC	20	50	kohm	$V_{IN} = V_{DDP}$
Input leakage current[9)]	I_{OZP}	CC	-1	1	µA	$0 < V_{IN} < V_{DDP}$, $T_A \leq 105$ °C
Voltage on any pin during V_{DDP} power off	V_{PO}	SR	–	0.3	V	[10)]
Maximum current per pin (excluding P1, V_{DDP} and V_{SS})	I_{MP}	SR	-10	11	mA	–
Maximum current per high currrent pins	I_{MP1A}	SR	-10	50	mA	–
Maximum current into V_{DDP} (TSSOP28/16, VQFN24)	I_{MVDD1}	SR	–	130	mA	[10)]
Maximum current into V_{DDP} (TSSOP38, VQFN40)	I_{MVDD2}	SR	–	260	mA	[10)]
Maximum current out of V_{SS} (TSSOP28/16, VQFN24)	I_{MVSS1}	SR	–	130	mA	[10)]
Maximum current out of V_{SS} (TSSOP38, VQFN40)	I_{MVSS2}	SR	–	260	mA	[10)]

1) Rise/Fall time parameters are taken with 10% - 90% of supply.
2) Additional rise/fall time valid for C_L = 50 pF - C_L = 100 pF @ 0.150 ns/pF at 5 V supply voltage.
3) Additional rise/fall time valid for C_L = 50 pF - C_L = 100 pF @ 0.205 ns/pF at 3.3 V supply voltage.
4) Additional rise/fall time valid for C_L = 50 pF - C_L = 100 pF @ 0.445 ns/pF at 1.8 V supply voltage.
5) Additional rise/fall time valid for C_L = 50 pF - C_L = 100 pF @ 0.225 ns/pF at 5 V supply voltage.
6) Additional rise/fall time valid for C_L = 50 pF - C_L = 100 pF @ 0.288 ns/pF at 3.3 V supply voltage.
7) Additional rise/fall time valid for C_L = 50 pF - C_L = 100 pF @ 0.588 ns/pF at 1.8 V supply voltage.

3.2.2 Analog to Digital Converters (ADC)

Table 17 shows the Analog to Digital Converter (ADC) characteristics.

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 17 ADC Characteristics (Operating Conditions apply)[1)]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Supply voltage range (internal reference)	V_{DD_int} SR	2.0	–	3.0	V	SHSCFG.AREF = 11_B CALCTR.CALGNSTC = $0C_H$
		3.0	–	5.5	V	SHSCFG.AREF = 10_B
Supply voltage range (external reference)	V_{DD_ext} SR	3.0	–	5.5	V	SHSCFG.AREF = 00_B
Analog input voltage range	V_{AIN} SR	V_{SSP} - 0.05	–	V_{DDP} + 0.05	V	
Auxiliary analog reference ground	V_{REFGND} SR	V_{SSP} - 0.05	–	1.0	V	G0CH0
Internal reference voltage (full scale value)	V_{REFINT} CC	5			V	
Switched capacitance of an analog input	C_{AINS} CC	–	1.2	2	pF	GNCTRxz.GAINy = 00_B (unity gain)
		–	1.2	2	pF	GNCTRxz.GAINy = 01_B (gain g1)
		–	4.5	6	pF	GNCTRxz.GAINy = 10_B (gain g2)
		–	4.5	6	pF	GNCTRxz.GAINy = 11_B (gain g3)
Total capacitance of an analog input	C_{AINT} CC	–	–	10	pF	
Total capacitance of the reference input	C_{AREFT} CC	–	–	10	pF	

Table 17 ADC Characteristics (Operating Conditions apply)[1)] (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gain settings	G_{IN} CC		1		–	GNCTRxz.GAINy = 00_B (unity gain)
			3		–	GNCTRxz.GAINy = 01_B (gain g1)
			6		–	GNCTRxz.GAINy = 10_B (gain g2)
			12		–	GNCTRxz.GAINy = 11_B (gain g3)
Sample Time	t_{sample} CC	4	–	–	1 / f_{ADC}	V_{DD} = 5.0 V
		4	–	–	1 / f_{ADC}	V_{DD} = 3.3 V
		30	–	–	1 / f_{ADC}	V_{DD} = 2.0 V
Sigma delta loop hold time	t_{SD_hold} CC	20	–	–	µs	Residual charge stored in an active sigma delta loop remains available
Conversion time in fast compare mode	t_{CF} CC		9		1 / f_{ADC}	[2)]
Conversion time in 12-bit mode	t_{C12} CC		20		1 / f_{ADC}	[2)]
Maximum sample rate in 12-bit mode [3)]	f_{C12} CC	–	–	f_{ADC} / 43.5	–	1 sample pending
		–	–	f_{ADC} / 63.5	–	2 samples pending
Conversion time in 10-bit mode	t_{C10} CC		18		1 / f_{ADC}	[2)]
Maximum sample rate in 10-bit mode [3)]	f_{C10} CC	–	–	f_{ADC} / 41.5	–	1 sample pending
		–	–	f_{ADC} / 59.5	–	2 samples pending
Conversion time in 8-bit mode	t_{C8} CC		16		1 / f_{ADC}	[2)]

3.2.3 Temperature Sensor Characteristics

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 18 Temperature Sensor Characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Measurement time	t_M CC	–	–	10	ms	
Temperature sensor range	T_{SR} SR	-40	–	115	°C	
Sensor Accuracy[1)]	T_{TSAL} CC	-6	–	6	°C	T_J > 20°C
		-10	–	10	°C	0°C ≤ T_J ≤ 20°C
		-18	–	18	°C	-25°C ≤ T_J < 0°C
		-31	–	31	°C	-40°C ≤ T_J < -25°C
Start-up time after enabling	t_{TSSTE} SR	–	–	15	µs	

1) The temperature sensor accuracy is independent of the supply voltage.

Table 19 Power Supply Parameters; V_{DDP} = 5V

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.[1]	Max.		
Sleep mode current Peripherals clock disabled Flash active f_{MCLK} / f_{PCLK} in MHz[5]	I_{DDPSD} CC	–	1.8	–	mA	32 / 64
			1.7	–	mA	24 / 48
			1.6	–	mA	16 / 32
			1.5	–	mA	8 / 16
			1.4	–	mA	1 / 1
Sleep mode current Peripherals clock disabled Flash powered down f_{MCLK} / f_{PCLK} in MHz[6]	I_{DDPSR} CC	–	1.2	–	mA	32 / 64
			1.1	–	mA	24 / 48
			1.0	–	mA	16 / 32
			0.8	–	mA	8 / 16
			0.7	–	mA	1 / 1
Deep Sleep mode current[7]	I_{DDPDS} CC	–	0.24	–	mA	
Wake-up time from Sleep to Active mode[8]	t_{SSA} CC	–	6	–	cycles	
Wake-up time from Deep Sleep to Active mode[9]	t_{DSA} CC	–	280	–	µsec	

1) The typical values are measured at T_A = + 25 °C and V_{DDP} = 5 V.
2) CPU and all peripherals clock enabled, Flash is in active mode.
3) CPU enabled, all peripherals clock disabled, Flash is in active mode.
4) CPU in sleep, all peripherals clock enabled and Flash is in active mode.
5) CPU in sleep, Flash is in active mode.
6) CPU in sleep, Flash is powered down and code executed from RAM after wake-up.
7) CPU in sleep, peripherals clock disabled, Flash is powered down and code executed from RAM after wake-up.
8) CPU in sleep, Flash is in active mode during sleep mode.
9) CPU in sleep, Flash is in powered down mode during deep sleep mode.

3.3 AC Parameters

3.3.1 Testing Waveforms

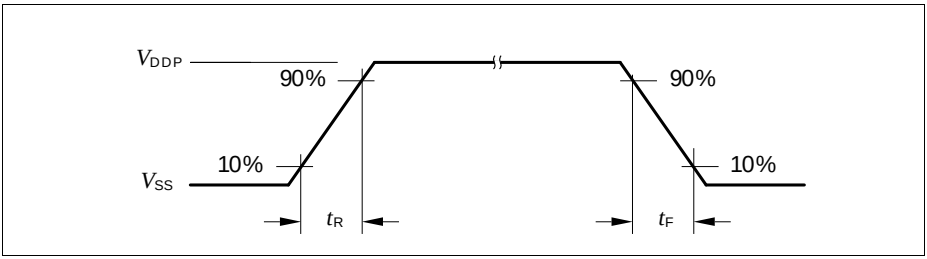

Figure 13 Rise/Fall Time Parameters

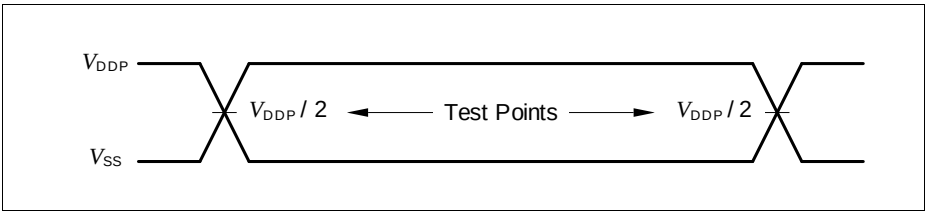

Figure 14 Testing Waveform, Output Delay

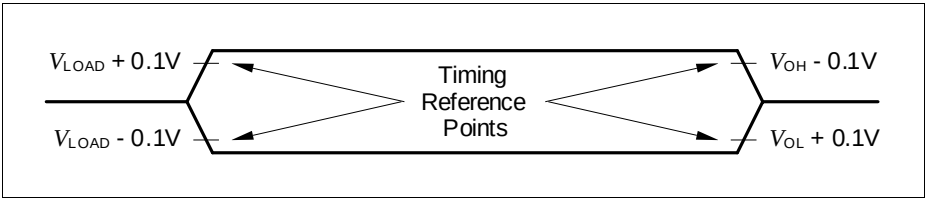

Figure 15 Testing Waveform, Output High Impedance

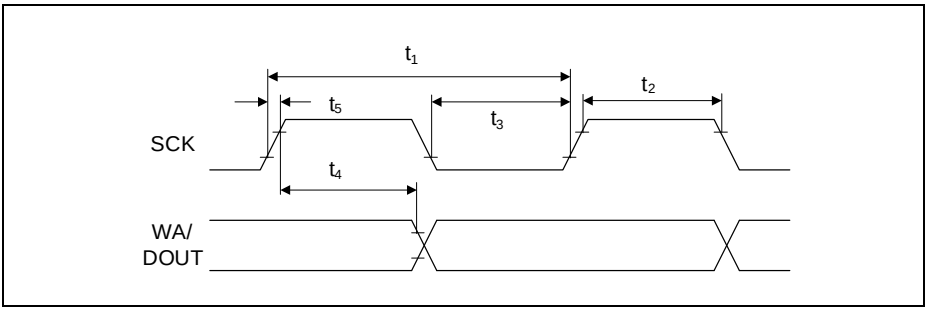

Figure 21 USIC IIS Master Transmitter Timing

Table 32 USIC IIS Slave Receiver Timing

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Clock period	t_6 SR	$4/f_{MCLK}$	-	-	ns	
Clock HIGH	t_7 SR	0.35 x t_{6min}	-	-	ns	
Clock Low	t_8 SR	0.35 x t_{6min}	-	-	ns	
Set-up time	t_9 SR	0.2 x t_{6min}	-	-	ns	
Hold time	t_{10} SR	10	-	-	ns	

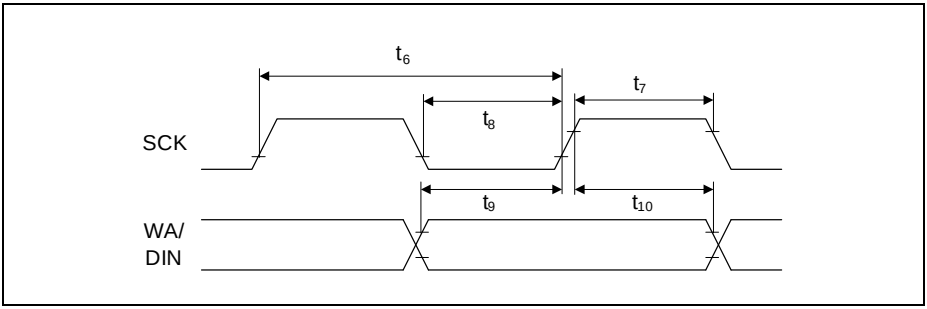

Figure 22 USIC IIS Slave Receiver Timing

The internal power consumption is defined as
$P_{INT} = V_{DDP} \times I_{DDP}$ (switching current and leakage current).

The static external power consumption caused by the output drivers is defined as
$P_{IOSTAT} = \Sigma((V_{DDP}-V_{OH}) \times I_{OH}) + \Sigma(V_{OL} \times I_{OL})$

The dynamic external power consumption caused by the output drivers (P_{IODYN}) depends on the capacitive load connected to the respective pins and their switching frequencies.

If the total power dissipation for a given system configuration exceeds the defined limit, countermeasures must be taken to ensure proper system operation:

- Reduce V_{DDP}, if possible in the system
- Reduce the system frequency
- Reduce the number of output pins
- Reduce the load on active output drivers

4.2 Package Outlines

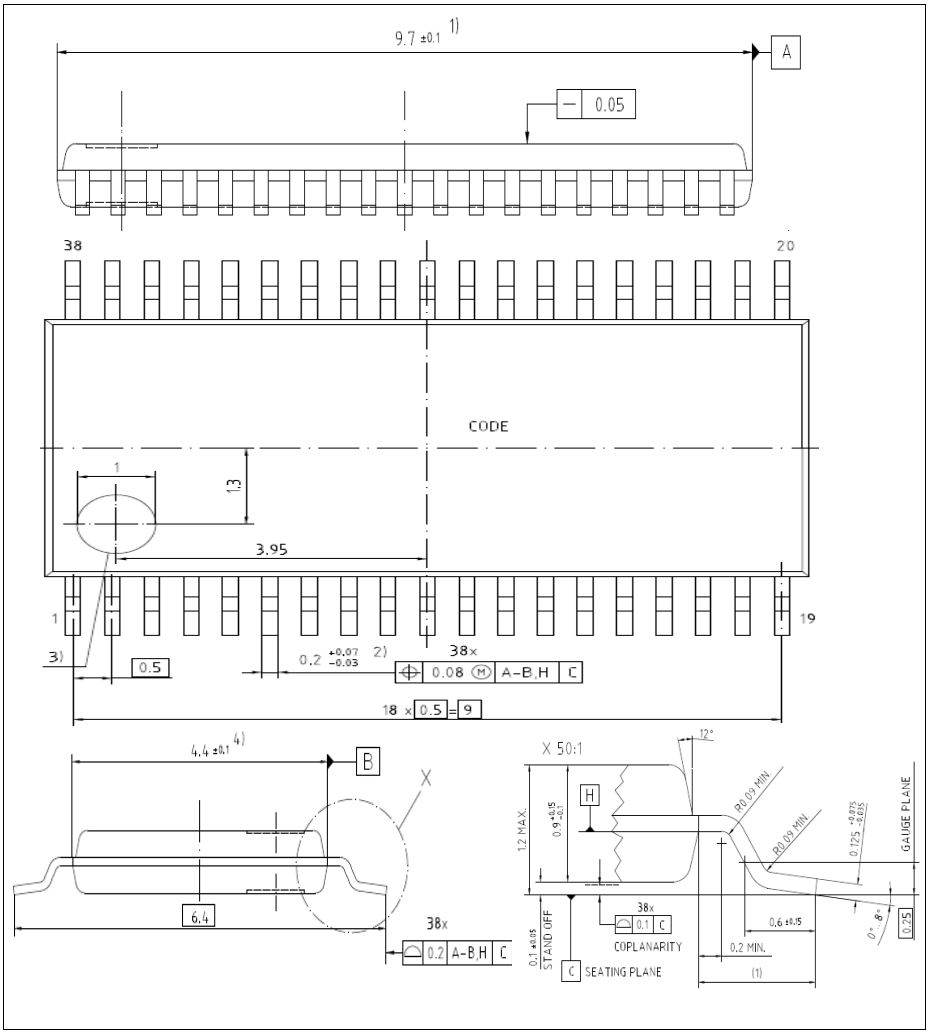

Figure 23 PG-TSSOP-38-9

5 Quality Declaration

Table 34 shows the characteristics of the quality parameters in the XMC1100.

Table 34 Quality Parameters

Parameter	Symbol	Limit Values		Unit	Notes
		Min.	Max.		
ESD susceptibility according to Human Body Model (HBM)	V_{HBM} SR	-	2000	V	Conforming to EIA/JESD22-A114-B
ESD susceptibility according to Charged Device Model (CDM) pins	V_{CDM} SR	-	500	V	Conforming to JESD22-C101-C
Moisture sensitivity level	MSL CC	-	3	-	JEDEC J-STD-020D
Soldering temperature	T_{SDR} SR	-	260	°C	Profile according to JEDEC J-STD-020D